

LASER DIODE AOC-1930-100

AOC-1930 is 1930nm laser diode based on GaInAsP/InP quantum well structure fabricated by MOCVD/MBE semiconductor laser. Low threshold current and high slope efficiency contribute to low operating current enhancing reliability.

AOC-1930 is delivered on an open sub-mount or in HHL sealed package with integrated TEC, thermistor and monitor diode to stabilise the power.. The laser diode(in any package) is suitable for application in medical and various other opto-electronic systems.

Optical and electrical characteristics (T = 25°C):

Operating parameters	Symbol	Min	Typ	Max	Unit
Optical output power	P _{out}	750	-	-	mW
Lasing wavelength	λ	1915	1930	1945	
Threshold current	I _{th}	500	900	1300	mA
Forward current	I _f		5	11	A
Forward voltage	U _f	1.0	1.5	1.6	V
Beam divergence parallel	$\Theta_{ }$	5	10	15	deg.
Beam divergence perpendicular	Θ_{\perp}	40	45	50	deg.
Spectral width (FWHM)	$\Delta\lambda$	3	9	15	nm
Mode structure		-	MM	-	-
Emitting area	W×H	100 × 1.5			μm
Cavity length	L		2000	2500	μm

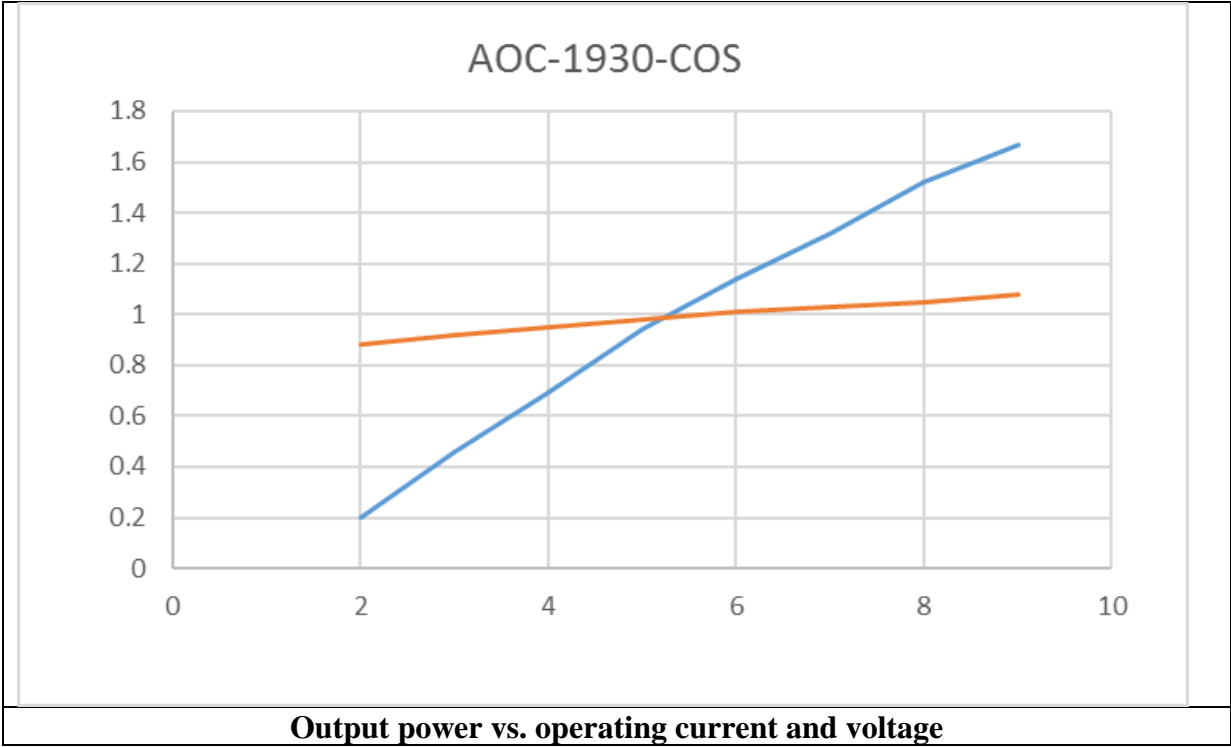
Additional information

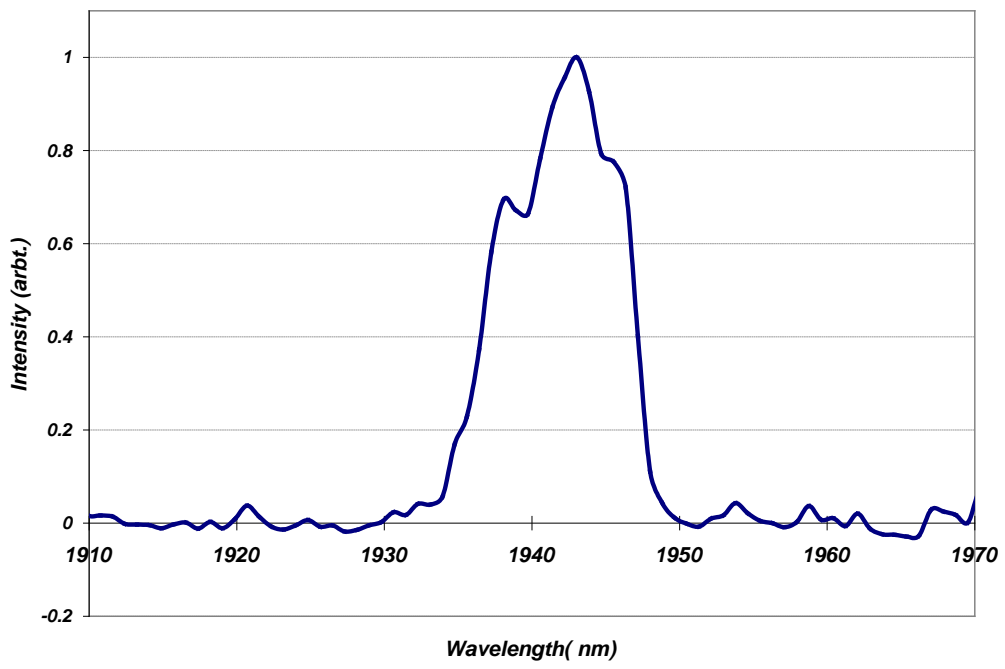
- - wavelength drift under temperature change <-0.4nm/°C;
- - operating temperature- 0°C +40°C;

Maximum Ratings

Operating Current	I _{op}	12 A
Reverse Voltage	VRVS	1.9V
Storage Temperature	T _{STG}	-30°C ~ 80°C
Soldering Temperature, max	T _{sold}	250°C
Relative Humidity, none noncondensing, ambient <45°C	RH	85%

TYPICAL PERFORMANCE





Emission spectrum

Package type chip on AlN submount,

Anode and cathode are electrically isolated from the bottom metallization

